## AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A semiconductor laser device, which is made from an AlGaInP-based material, comprising:

a first clad layer of a first conductivity type, an active layer and a second clad layer of a second conductivity type that are formed over a semiconductor substrate,

wherein a portion of said active layer in an area near a laser resonator end face has a peak wavelength in photoluminescence that is smaller than a peak wavelength in photoluminescence in a portion of said active layer in a laser resonator inner area and contains impurity atoms having the second conductivity, contained in the second clad layer of the second conductivity type,

the second clad layer of the second conductivity type located in the area near a laser resonator end face contains As atoms, and

impurity atoms having the second conductivity, contained in the second clad layer of the second conductivity type in the area near a laser resonator end face, are the same as impurity atoms having the second conductivity contained in the second clad layer of the second conductivity type in the laser resonator inner area, and the impurity atoms having the second conductivity, contained in the second clad layer of the second conductivity type in the area near a laser resonator end face and the laser resonator inner area, are II-group atoms that have an atomic number smaller than the atomic number of P.

2. (Previously Presented) The semiconductor laser device according to claim 1,

wherein the As atom concentration in the second clad layer of the second conductivity type in the area near a laser resonator end face is higher than an As atom concentration in the second clad layer of the second conductivity type in the laser resonator inner area.

3. (Previously Presented) The semiconductor laser device according to claim 1 or 2, wherein the As atom concentration in the second clad layer of the second conductivity type in the area near a laser resonator end face is in a range from not less than $1 \times 10^{18}cm^{-3}$ to not more than $1 \times 10^{20}cm^{-3}$.

4-5 (Canceled)

6. (Previously Presented) The semiconductor laser device according to claim 1, wherein II-group atoms are Be atoms.

7. (Previously Presented) The semiconductor laser device according to claim 1, wherein the impurity atoms having the second conductivity, contained in the second clad layer of the second conductivity type in the area near a laser resonator end face and the laser resonator inner area have a concentration in a range from not less than $1 \times 10^{18}$ atoms/cm$^{-3}$ to not more than $5 \times 10^{18}$ atoms/cm$^{-3}$.

8. (Previously Presented) The semiconductor laser device according to claim 1 or 2, further comprising a GaAs contact layer of the second conductivity type formed over the second clad layer of the second conductivity type in the area near a laser resonator end face and the laser resonator inner area, and a GaInP intermediate layer of the second conductivity type formed between the second clad layer of the second conductivity type and the GaAs contact layer of the second conductivity type in the laser resonator inner area.

9. (Previously Presented) The semiconductor laser device according to claim 1 or 2, wherein a GaAs current non-injection layer of the second conductivity type is formed over the second clad layer of the second conductivity type in the area near a laser resonator end face.

10-17. (Canceled)

18. (Previously Presented) The semiconductor laser device according to claim 6, wherein the impurity atoms having the second conductivity, contained in the second clad layer of the second conductivity type in the area near a laser resonator end face and the laser resonator inner area have a concentration in a range from not less than $1 \times 10^{18}$ atoms/cm$^{-3}$ to not more than $5 \times 10^{18}$ atoms/cm$^{-3}$.

19. (Previously Presented) The semiconductor laser device according to claim 3, further comprising a GaAs contact layer of the second conductivity type formed over the second clad layer of the second conductivity type in the area near a laser resonator end face and the laser resonator inner area, and a GaInP intermediate layer of the second conductivity type formed between the second clad layer of the second conductivity type and the GaAs contact layer of the second conductivity type in the laser resonator inner area.

20. (Canceled)

21. (Previously Presented) The semiconductor laser device according to claim 6, further comprising a GaAs contact layer of the second conductivity type formed over the second clad layer

of the second conductivity type in the area near a laser resonator end face and the laser resonator inner area, and a GaInP intermediate layer of the second conductivity type formed between the second clad layer of the second conductivity type and the GaAs contact layer of the second conductivity type in the laser resonator inner area.

22. (Previously Presented) The semiconductor laser device according to claim 7, further comprising a GaAs contact layer of the second conductivity type formed over the second clad layer of the second conductivity type in the area near a laser resonator end face and the laser resonator inner area, and a GaInP intermediate layer of the second conductivity type formed between the second clad layer of the second conductivity type and the GaAs contact layer of the second conductivity type in the laser resonator inner area.